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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	1176
Number of Logic Elements/Cells	5292
Total RAM Bits	57344
Number of I/O	140
Number of Gates	200000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc2s200-6pqg208c

Spartan-II Product Availability

Table 2 shows the maximum user I/Os available on the device and the number of user I/Os available for each device/package combination. The four global clock pins are usable as additional user I/Os when not used as a global clock pin. These pins are not included in user I/O counts.

Table 2: **Spartan-II FPGA User I/O Chart**(1)

Device	Maximum User I/O	Available User I/O According to Package Type					
		VQ100 VQG100	TQ144 TQG144	CS144 CSG144	PQ208 PQG208	FG256 FGG256	FG456 FGG456
XC2S15	86	60	86	(Note 2)	-	-	-
XC2S30	92	60	92	92	(Note 2)	-	-
XC2S50	176	-	92	-	140	176	-
XC2S100	176	-	92	-	140	176	(Note 2)
XC2S150	260	-	-	-	140	176	260
XC2S200	284	-	-	-	140	176	284

Notes:
1. All user I/O counts do not include the four global clock/user input pins.
2. Discontinued by PDN2004-01.

Revision History

Date	Version No.	Description
09/18/00	2.0	Sectioned the Spartan-II Family data sheet into four modules. Added industrial temperature range information.
10/31/00	2.1	Removed Power down feature.
03/05/01	2.2	Added statement on PROMs.
11/01/01	2.3	Updated Product Availability chart. Minor text edits.
09/03/03	2.4	Added device part marking.
08/02/04	2.5	Added information on Pb-free packaging options and removed discontinued options.
06/13/08	2.8	Updated description and links. Updated all modules for continuous page, figure, and table numbering. Synchronized all modules to v2.8.

PN 011311

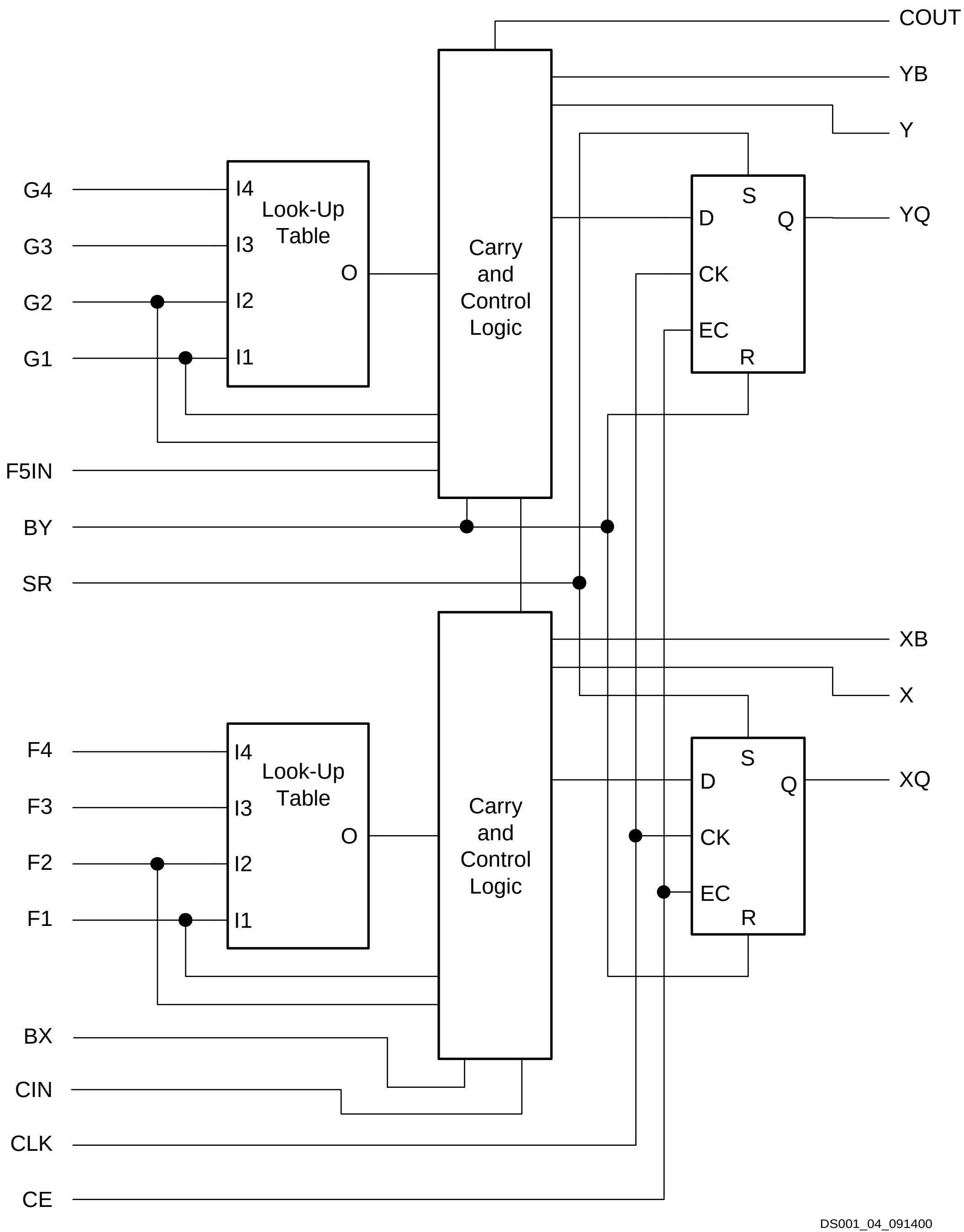


Figure 4: **Spartan-II CLB Slice** (two identical slices in each CLB)

Storage Elements

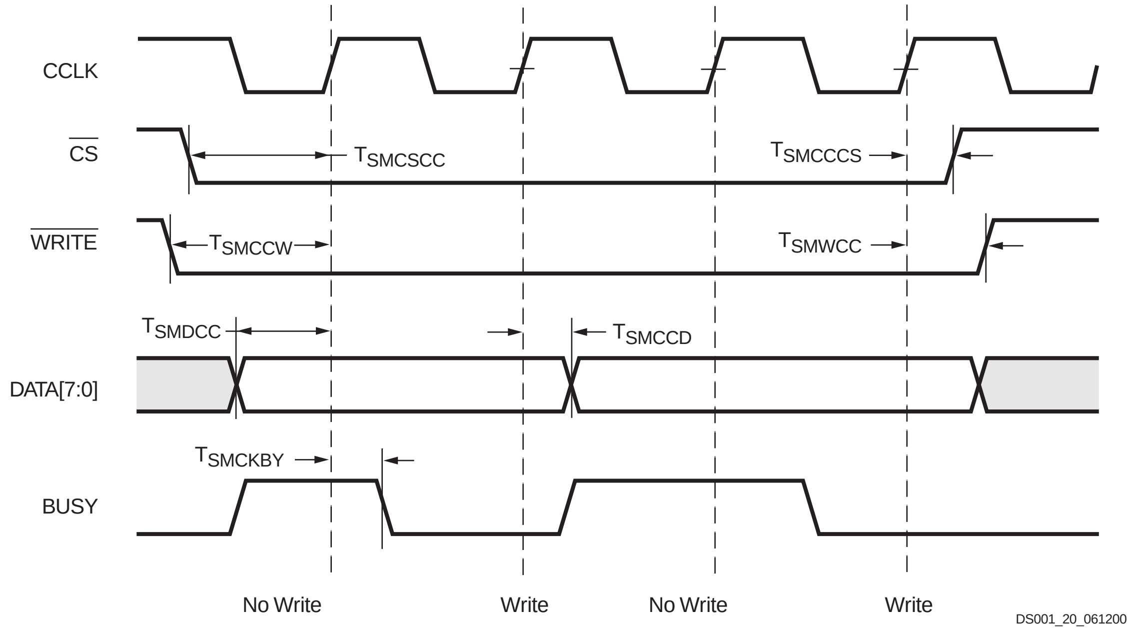
Storage elements in the Spartan-II FPGA slice can be configured either as edge-triggered D-type flip-flops or as level-sensitive latches. The D inputs can be driven either by function generators within the slice or directly from slice inputs, bypassing the function generators.

In addition to Clock and Clock Enable signals, each slice has synchronous set and reset signals (SR and BY). SR forces a storage element into the initialization state specified for it in the configuration. BY forces it into the opposite state. Alternatively, these signals may be configured to operate asynchronously.

All control signals are independently invertible, and are shared by the two flip-flops within the slice.

Additional Logic

The F5 multiplexer in each slice combines the function generator outputs. This combination provides either a function generator that can implement any 5-input function, a 4:1 multiplexer, or selected functions of up to nine inputs.



Symbol		Description		Units
T_{SMDCC}	CCLK	D0-D7 setup/hold	5	ns, min
T_{SMCCD}		D0-D7 hold	0	ns, min
T_{SMCSCC}		$\overline{\text{CS}}$ setup	7	ns, min
T_{SMCCCS}		$\overline{\text{CS}}$ hold	0	ns, min
T_{SMCCW}		$\overline{\text{WRITE}}$ setup	7	ns, min
T_{SMWCC}		$\overline{\text{WRITE}}$ hold	0	ns, min
T_{SMCKBY}		BUSY propagation delay	12	ns, max
F_{CC}		Maximum frequency	66	MHz, max
F_{CCNH}		Maximum frequency with no handshake	50	MHz, max

Figure 20: **Slave Parallel Write Timing**

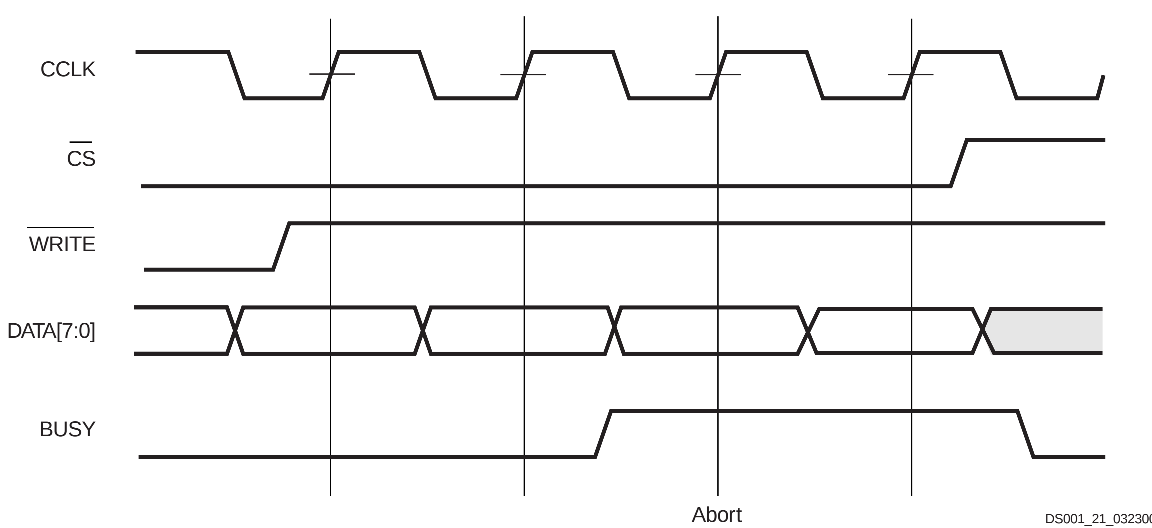


Figure 21: **Slave Parallel Write Abort Waveforms**

support of a wide variety of applications, from general purpose standard applications to high-speed low-voltage memory busses.

Versatile I/O blocks also provide selectable output drive strengths and programmable slew rates for the LVTTL output buffers, as well as an optional, programmable weak pull-up, weak pull-down, or weak "keeper" circuit ideal for use in external bussing applications.

Each Input/Output Block (IOB) includes three registers, one each for the input, output, and 3-state signals within the IOB. These registers are optionally configurable as either a D-type flip-flop or as a level sensitive latch.

The input buffer has an optional delay element used to guarantee a zero hold time requirement for input signals registered within the IOB.

The Versatile I/O features also provide dedicated resources for input reference voltage (V_{REF}) and output source voltage (V_{CCO}), along with a convenient banking system that simplifies board design.

By taking advantage of the built-in features and wide variety of I/O standards supported by the Versatile I/O features, system-level design and board design can be greatly simplified and improved.

Fundamentals

Modern bus applications, pioneered by the largest and most influential companies in the digital electronics industry, are commonly introduced with a new I/O standard tailored specifically to the needs of that application. The bus I/O standards provide specifications to other vendors who create products designed to interface with these applications. Each standard often has its own specifications for current, voltage, I/O buffering, and termination techniques.

The ability to provide the flexibility and time-to-market advantages of programmable logic is increasingly dependent on the capability of the programmable logic device to support an ever increasing variety of I/O standards

The Versatile I/O resources feature highly configurable input and output buffers which provide support for a wide variety of I/O standards. As shown in Table 15, each buffer type can support a variety of voltage requirements.

Table 15: **Versatile I/O Supported Standards (Typical Values)**

I/O Standard	Input Reference Voltage (V_{REF})	Output Source Voltage (V_{CCO})	Board Termination Voltage (V_{TT})
LVTTL (2-24 mA)	N/A	3.3	N/A
LVCMOS2	N/A	2.5	N/A
PCI (3V/5V, 33 MHz/66 MHz)	N/A	3.3	N/A
GTL	0.8	N/A	1.2
GTL+	1.0	N/A	1.5
HSTL Class I	0.75	1.5	0.75
HSTL Class III	0.9	1.5	1.5
HSTL Class IV	0.9	1.5	1.5
SSTL3 Class I and II	1.5	3.3	1.5
SSTL2 Class I and II	1.25	2.5	1.25
CTT	1.5	3.3	1.5
AGP-2X	1.32	3.3	N/A

Overview of Supported I/O Standards

This section provides a brief overview of the I/O standards supported by all Spartan-II devices.

While most I/O standards specify a range of allowed voltages, this document records typical voltage values only. Detailed information on each specification may be found on the Electronic Industry Alliance JEDEC website at http://www.jedec.org. For more details on the I/O standards and termination application examples, see XAPP179, "*Using SelectIO Interfaces in Spartan-II and Spartan-IIE FPGAs.*"

LVTTL — Low-Voltage TTL

The Low-Voltage TTL (LVTTL) standard is a general purpose EIA/JESDSA standard for 3.3V applications that uses an LVTTL input buffer and a Push-Pull output buffer. This standard requires a 3.3V output source voltage (V_{CCO}), but does not require the use of a reference voltage (V_{REF}) or a termination voltage (V_{TT}).

LVCMOS2 — Low-Voltage CMOS for 2.5V

The Low-Voltage CMOS for 2.5V or lower (LVCMOS2) standard is an extension of the LVCMOS standard (JESD 8.5) used for general purpose 2.5V applications. This standard requires a 2.5V output source voltage (V_{CCO}), but does not require the use of a reference voltage (V_{REF}) or a board termination voltage (V_{TT}).

LVTTL output buffers have selectable drive strengths.

The format for LVTTL OBUF primitive names is as follows.

OBUF_<slew_rate>_<drive_strength>

<slew_rate> is either F (Fast), or S (Slow) and <drive_strength> is specified in milliamps (2, 4, 6, 8, 12, 16, or 24). The default is slew rate limited with 12 mA drive.

OBUF placement restrictions require that within a given V_{CCO} bank each OBUF share the same output source drive voltage. Input buffers of any type and output buffers that do not require V_{CCO} can be placed within any V_{CCO} bank. Table 17 summarizes the output compatibility requirements. The LOC property can specify a location for the OBUF.

Table 17: **Output Standards Compatibility Requirements**

Rule 1	Only outputs with standards which share compatible V_{CCO} may be used within the same bank.
Rule 2	There are no placement restrictions for outputs with standards that do not require a V_{CCO}.
V_{CCO}	Compatible Standards
3.3	LVTTL, SSTL3_I, SSTL3_II, CTT, AGP, GTL, GTL+, PCI33_3, PCI66_3
2.5	SSTL2_I, SSTL2_II, LVCMOS2, GTL, GTL+
1.5	HSTL_I, HSTL_III, HSTL_IV, GTL, GTL+

OBUFT

The generic 3-state output buffer OBUFT, shown in Figure 39, typically implements 3-state outputs or bidirectional I/O.

With no extension or property specified for the generic OBUFT primitive, the assumed standard is slew rate limited LVTTL with 12 mA drive strength.

The LVTTL OBUFT can support one of two slew rate modes to minimize bus transients. By default, the slew rate for each output buffer is reduced to minimize power bus transients when switching non-critical signals.

LVTTL 3-state output buffers have selectable drive strengths.

The format for LVTTL OBUFT primitive names is as follows.

OBUFT_<slew_rate>_<drive_strength>

<slew_rate> can be either F (Fast), or S (Slow) and <drive_strength> is specified in milliamps (2, 4, 6, 8, 12, 16, or 24).

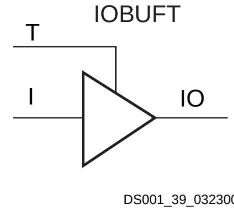


Figure 39: **3-State Output Buffer Primitive (OBUFT**

The Versatile I/O OBUFT placement restrictions require that within a given V_{CCO} bank each OBUFT share the same output source drive voltage. Input buffers of any type and output buffers that do not require V_{CCO} can be placed within the same V_{CCO} bank.

The LOC property can specify a location for the OBUFT.

3-state output buffers and bidirectional buffers can have either a weak pull-up resistor, a weak pull-down resistor, or a weak "keeper" circuit. Control this feature by adding the appropriate primitive to the output net of the OBUFT (PULLUP, PULLDOWN, or KEEPER).

The weak "keeper" circuit requires the input buffer within the IOB to sample the I/O signal. So, OBUFTs programmed for an I/O standard that requires a V_{REF} have automatic placement of a V_{REF} in the bank with an OBUFT configured with a weak "keeper" circuit. This restriction does not affect most circuit design as applications using an OBUFT configured with a weak "keeper" typically implement a bidirectional I/O. In this case the IBUF (and the corresponding V_{REF}) are explicitly placed.

The LOC property can specify a location for the OBUFT.

IOBUF

Use the IOBUF primitive for bidirectional signals that require both an input buffer and a 3-state output buffer with an active high 3-state pin. The generic input/output buffer IOBUF appears in Figure 40.

With no extension or property specified for the generic IOBUF primitive, the assumed standard is LVTTL input buffer and slew rate limited LVTTL with 12 mA drive strength for the output buffer.

The LVTTL IOBUF can support one of two slew rate modes to minimize bus transients. By default, the slew rate for each output buffer is reduced to minimize power bus transients when switching non-critical signals.

LVTTL bidirectional buffers have selectable output drive strengths.

The format for LVTTL IOBUF primitive names is as follows:

property. This property could have one of the following seven values.

DRIVE=2

DRIVE=4

DRIVE=6

DRIVE=8

DRIVE=12 (Default)

DRIVE=16

DRIVE=24

Design Considerations

Reference Voltage (V_{REF}) Pins

Low-voltage I/O standards with a differential amplifier input buffer require an input reference voltage (V_{REF}). Provide the V_{REF} as an external signal to the device.

The voltage reference signal is "banked" within the device on a half-edge basis such that for all packages there are eight independent V_{REF} banks internally. See Figure 36, page 39 for a representation of the I/O banks. Within each bank approximately one of every six I/O pins is automatically configured as a V_{REF} input.

Within each V_{REF} bank, any input buffers that require a V_{REF} signal must be of the same type. Output buffers of any type and input buffers can be placed without requiring a reference voltage within the same V_{REF} bank.

Output Drive Source Voltage (V_{CCO}) Pins

Many of the low voltage I/O standards supported by Versatile I/Os require a different output drive source voltage (V_{CCO}). As a result each device can often have to support multiple output drive source voltages.

The V_{CCO} supplies are internally tied together for some packages. The VQ100 and the PQ208 provide one combined V_{CCO} supply. The TQ144 and the CS144 packages provide four independent V_{CCO} supplies. The FG256 and the FG456 provide eight independent V_{CCO} supplies.

Output buffers within a given V_{CCO} bank must share the same output drive source voltage. Input buffers for LVTTL, LVCMOS2, PCI33_3, and PCI 66_3 use the V_{CCO} voltage for Input V_{CCO} voltage.

Transmission Line Effects

The delay of an electrical signal along a wire is dominated by the rise and fall times when the signal travels a short distance. Transmission line delays vary with inductance and capacitance, but a well-designed board can experience delays of approximately 180 ps per inch.

Transmission line effects, or reflections, typically start at 1.5" for fast (1.5 ns) rise and fall times. Poor (or non-existent) termination or changes in the transmission line impedance cause these reflections and can cause additional delay in longer traces. As system speeds continue to increase, the effect of I/O delays can become a limiting factor and therefore transmission line termination becomes increasingly more important.

Termination Techniques

A variety of termination techniques reduce the impact of transmission line effects.

The following lists output termination techniques:

None
Series
Parallel (Shunt)
Series and Parallel (Series-Shunt)

Input termination techniques include the following:

None
Parallel (Shunt)

These termination techniques can be applied in any combination. A generic example of each combination of termination methods appears in Figure 41.

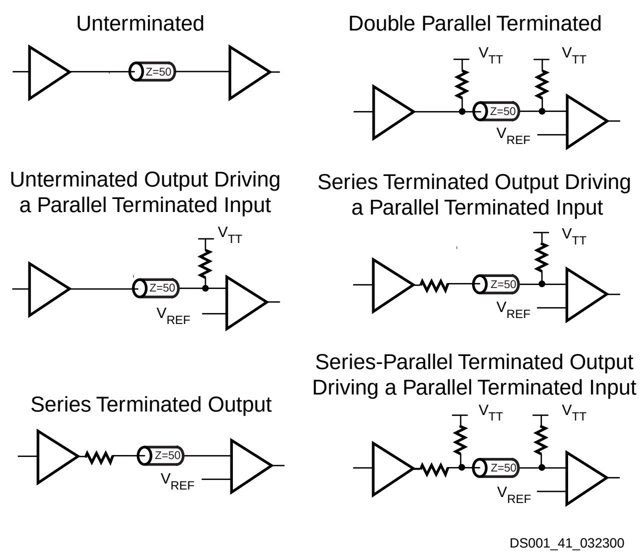


Figure 41: **Overview of Standard Input and Output Termination Methods**

Simultaneous Switching Guidelines

Ground bounce can occur with high-speed digital ICs when multiple outputs change states simultaneously, causing undesired transient behavior on an output, or in the internal logic. This problem is also referred to as the Simultaneous Switching Output (SSO) problem.

Ground bounce is primarily due to current changes in the combined inductance of ground pins, bond wires, and

GTL

A sample circuit illustrating a valid termination technique for GTL is shown in Figure 42. Table 20 lists DC voltage specifications for the GTL standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

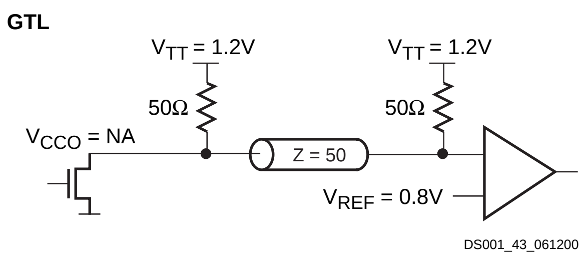


Figure 42: **Terminated GTL**

Table 20: **GTL Voltage Specifications**

Parameter	Min	Typ	Max
V_{CCO}	-	N/A	-
$V_{REF} = N \times V_{TT}^{(1)}$	0.74	0.8	0.86
V_{TT}	1.14	1.2	1.26
$V_{IH} \geq V_{REF} + 0.05$	0.79	0.85	-
$V_{IL} \leq V_{REF} - 0.05$	-	0.75	0.81
V_{OH}	-	-	-
V_{OL}	-	0.2	0.4
I_{OH} at V_{OH} (mA)	-	-	-
I_{OL} at V_{OL} (mA) at 0.4V	32	-	-
I_{OL} at V_{OL} (mA) at 0.2V	-	-	40

Notes:
1. N must be greater than or equal to 0.653 and less than or equal to 0.68.

GTL+

A sample circuit illustrating a valid termination technique for GTL+ appears in Figure 43. DC voltage specifications appear in Table 21 for the GTL+ standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

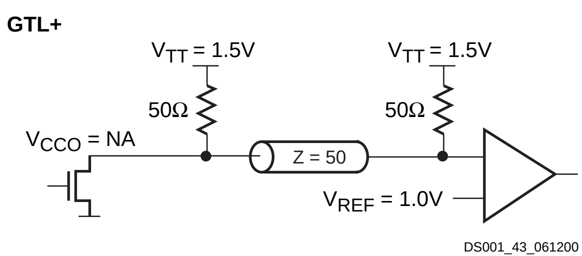


Figure 43: **Terminated GTL+**

Table 21: **GTL+ Voltage Specifications**

Parameter	Min	Typ	Max
V_{CCO}	-	-	-
$V_{REF} = N \times V_{TT}^{(1)}$	0.88	1.0	1.12
V_{TT}	1.35	1.5	1.65
$V_{IH} \geq V_{REF} + 0.1$	0.98	1.1	-
$V_{IL} \leq V_{REF} - 0.1$	-	0.9	1.02
V_{OH}	-	-	-
V_{OL}	0.3	0.45	0.6
I_{OH} at V_{OH} (mA)	-	-	-
I_{OL} at V_{OL} (mA) at 0.6V	36	-	-
I_{OL} at V_{OL} (mA) at 0.3V	-	-	48

Notes:
1. N must be greater than or equal to 0.653 and less than or equal to 0.68.

HSTL Class I

A sample circuit illustrating a valid termination technique for HSTL_I appears in Figure 44. DC voltage specifications appear in Table 22 for the HSTL_1 standard. See "DC Specifications" in Module 3 for the actual FPGA characteristics.

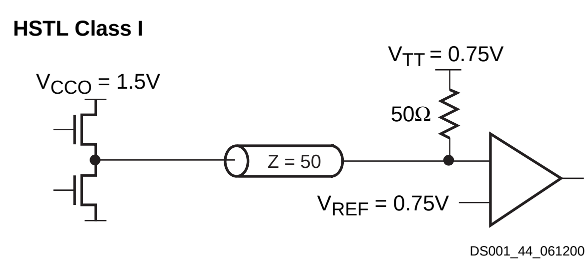


Figure 44: **Terminated HSTL Class I**

Table 22: **HSTL Class I Voltage Specification**

Parameter	Min	Typ	Max
V_{CCO}	1.40	1.50	1.60
V_{REF}	0.68	0.75	0.90
V_{TT}	-	$V_{CCO} \times 0.5$	-
V_{IH}	$V_{REF} + 0.1$	-	-
V_{IL}	-	-	$V_{REF} - 0.1$
V_{OH}	$V_{CCO} - 0.4$	-	-
V_{OL}			0.4
I_{OH} at V_{OH} (mA)	–8	-	-
I_{OL} at V_{OL} (mA)	8	-	-

Recommended Operating Conditions

Symbol	Description		Min	Max	Units
T_J	Junction temperature(1)	Commercial	0	85	°C
		Industrial	–40	100	°C
V_{CCINT}	Supply voltage relative to GND(2,5)	Commercial	2.5 – 5%	2.5 + 5%	V
		Industrial	2.5 – 5%	2.5 + 5%	V
V_{CCO}	Supply voltage relative to GND(3,5)	Commercial	1.4	3.6	V
		Industrial	1.4	3.6	V
T_{IN}	Input signal transition time(4)		-	250	ns

Notes:
1. At junction temperatures above those listed as Operating Conditions, all delay parameters increase by 0.35% per °C.
2. Functional operation is guaranteed down to a minimum V_{CCINT} of 2.25V (Nominal V_{CCINT} – 10%). For every 50 mV reduction in V_{CCINT} below 2.375V (nominal V_{CCINT} – 5%), all delay parameters increase by 3%.
3. Minimum and maximum values for V_{CCO} vary according to the I/O standard selected.
4. Input and output measurement threshold is ~50% of V_{CCO}. See "Delay Measurement Methodology," page 60 for specific levels.
5. Supply voltages may be applied in any order desired.

DC Characteristics Over Operating Conditions

Symbol	Description			Min	Typ	Max	Units
V_{DRINT}	Data Retention V_{CCINT} voltage (below which configuration data may be lost)			2.0	-	-	V
V_{DRIO}	Data Retention V_{CCO} voltage (below which configuration data may be lost)			1.2	-	-	V
I_{CCINTQ}	Quiescent V_{CCINT} supply current(1)	XC2S15	Commercial	-	10	30	mA
			Industrial	-	10	60	mA
		XC2S30	Commercial	-	10	30	mA
			Industrial	-	10	60	mA
		XC2S50	Commercial	-	12	50	mA
			Industrial	-	12	100	mA
		XC2S100	Commercial	-	12	50	mA
			Industrial	-	12	100	mA
		XC2S150	Commercial	-	15	50	mA
			Industrial	-	15	100	mA
		XC2S200	Commercial	-	15	75	mA
			Industrial	-	15	150	mA
I_{CCOQ}	Quiescent V_{CCO} supply current(1)			-	-	2	mA
I_{REF}	V_{REF} current per V_{REF} pin			-	-	20	µA
I_L	Input or output leakage current(2)			–10	-	+10	µA
C_{IN}	Input capacitance (sample tested)	VQ, CS, TQ, PQ, FG packages		-	-	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V (sample tested)(3)			-	-	0.25	mA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.6V (sample tested)(3)			-	-	0.15	mA

Notes:
1. With no output current loads, no active input pull-up resistors, all I/O pins 3-stated and floating.
2. The I/O leakage current specification applies only when the V_{CCINT} and V_{CCO} supply voltages have reached their respective minimum Recommended Operating Conditions.
3. Internal pull-up and pull-down resistors guarantee valid logic levels at unconnected input pins. These pull-up and pull-down resistors do not provide valid logic levels when input pins are connected to other circuits.

IOB Input Delay Adjustments for Different Standards[1]

Input delays associated with the pad are specified for LVTTL. For other standards, adjust the delays by the values shown. A delay adjusted in this way constitutes a worst-case limit.

Symbol	Description	Standard	Speed Grade		Units
			-6	-5	
Data Input Delay Adjustments					
T_{ILVTTL}	Standard-specific data input delay adjustments	LVTTL	0	0	ns
$T_{ILVCMOS2}$		LVCMOS2	–0.04	–0.05	ns
T_{IPCI33_3}		PCI, 33 MHz, 3.3V	–0.11	–0.13	ns
T_{IPCI33_5}		PCI, 33 MHz, 5.0V	0.26	0.30	ns
T_{IPCI66_3}		PCI, 66 MHz, 3.3V	–0.11	–0.13	ns
T_{IGTL}		GTL	0.20	0.24	ns
T_{IGTLP}		GTL+	0.11	0.13	ns
T_{IHSTL}		HSTL	0.03	0.04	ns
T_{ISSTL2}		SSTL2	–0.08	–0.09	ns
T_{ISSTL3}		SSTL3	–0.04	–0.05	ns
T_{ICTT}		CTT	0.02	0.02	ns
T_{IAGP}		AGP	–0.06	–0.07	ns

Notes:
1. Input timing for LVTTL is measured at 1.4V. For other I/O standards, see the table "Delay Measurement Methodology," page 60.

IOB Output Switching Characteristics

Output delays terminating at a pad are specified for LVTTL with 12 mA drive and fast slew rate. For other standards, adjust the delays with the values shown in "IOB Output Delay Adjustments for Different Standards," page 59.

Symbol	Description	Speed Grade				Units
		-6		-5		
		Min	Max	Min	Max	
Propagation Delays						
T_{IOOP}	O input to pad	-	2.9	-	3.4	ns
T_{IOOLP}	O input to pad via transparent latch	-	3.4	-	4.0	ns
3-state Delays						
T_{IOTHZ}	T input to pad high-impedance(1)	-	2.0	-	2.3	ns
T_{IOTON}	T input to valid data on pad	-	3.0	-	3.6	ns
$T_{IOTLPHZ}$	T input to pad high impedance via transparent latch(1)	-	2.5	-	2.9	ns
$T_{IOTLPON}$	T input to valid data on pad via transparent latch	-	3.5	-	4.2	ns
T_{GTS}	GTS to pad high impedance(1)	-	5.0	-	5.9	ns
Sequential Delays						
T_{IOCKP}	Clock CLK to pad	-	2.9	-	3.4	ns
T_{IOCKHZ}	Clock CLK to pad high impedance (synchronous)(1)	-	2.3	-	2.7	ns
T_{IOCKON}	Clock CLK to valid data on pad (synchronous)	-	3.3	-	4.0	ns
Setup/Hold Times with Respect to Clock CLK(2)						
T_{IOOCK} / T_{IOCKO}	O input	1.1 / 0	-	1.3 / 0	-	ns
$T_{IOOCECK}$ / $T_{IOCKOCE}$	OCE input	0.9 / 0.01	-	0.9 / 0.01	-	ns
$T_{IOSRCKO}$ / $T_{IOCKOSR}$	SR input (OFF)	1.2 / 0	-	1.3 / 0	-	ns
T_{IOTCK} / T_{IOCKT}	3-state setup times, T input	0.8 / 0	-	0.9 / 0	-	ns
$T_{IOTCECK}$ / $T_{IOCKTCE}$	3-state setup times, TCE input	1.0 / 0	-	1.0 / 0	-	ns
$T_{IOSRCKT}$ / $T_{IOCKTSR}$	3-state setup times, SR input (TFF)	1.1 / 0	-	1.2 / 0	-	ns
Set/Reset Delays						
T_{IOSRP}	SR input to pad (asynchronous)	-	3.7	-	4.4	ns
T_{IOSRHZ}	SR input to pad high impedance (asynchronous)(1)	-	3.1	-	3.7	ns
T_{IOSRON}	SR input to valid data on pad (asynchronous)	-	4.1	-	4.9	ns
T_{IOGSRQ}	GSR to pad	-	9.9	-	11.7	ns

Notes:
1. Three-state turn-off delays should not be adjusted.
2. A zero hold time listing indicates no hold time or a negative hold time.

IOB Output Delay Adjustments for Different Standards(1)

Output delays terminating at a pad are specified for LVTTL with 12 mA drive and fast slew rate. For other standards, adjust the delays by the values shown. A delay adjusted in this way constitutes a worst-case limit.

Symbol	Description	Standard	Speed Grade -6	Speed Grade -5	Units
Output Delay Adjustments (Adj)					
T_{OLVTTL_S2}	Standard-specific adjustments for output delays terminating at pads (based on standard capacitive load, C_{SL})	LVTTL, Slow, 2 mA	14.2	16.9	ns
T_{OLVTTL_S4}		4 mA	7.2	8.6	ns
T_{OLVTTL_S6}		6 mA	4.7	5.5	ns
T_{OLVTTL_S8}		8 mA	2.9	3.5	ns
T_{OLVTTL_S12}		12 mA	1.9	2.2	ns
T_{OLVTTL_S16}		16 mA	1.7	2.0	ns
T_{OLVTTL_S24}		24 mA	1.3	1.5	ns
T_{OLVTTL_F2}		LVTTL, Fast, 2 mA	12.6	15.0	ns
T_{OLVTTL_F4}		4 mA	5.1	6.1	ns
T_{OLVTTL_F6}		6 mA	3.0	3.6	ns
T_{OLVTTL_F8}		8 mA	1.0	1.2	ns
T_{OLVTTL_F12}		12 mA	0	0	ns
T_{OLVTTL_F16}		16 mA	–0.1	–0.1	ns
T_{OLVTTL_F24}		24 mA	–0.1	–0.2	ns
$T_{OLVCMOS2}$		LVCMOS2	0.2	0.2	ns
T_{OPCI33_3}		PCI, 33 MHz, 3.3V	2.4	2.9	ns
T_{OPCI33_5}		PCI, 33 MHz, 5.0V	2.9	3.5	ns
T_{OPCI66_3}		PCI, 66 MHz, 3.3V	–0.3	–0.4	ns
T_{OGTL}		GTL	0.6	0.7	ns
T_{OGTLP}		GTL+	0.9	1.1	ns
T_{OHSTL_I}		HSTL I	–0.4	–0.5	ns
T_{OHSTL_III}		HSTL III	–0.8	–1.0	ns
T_{OHSTL_IV}		HSTL IV	–0.9	–1.1	ns
T_{OSSTL2_I}		SSTL2 I	–0.4	–0.5	ns
T_{OSSLT2_II}		SSTL2 II	–0.8	–1.0	ns
T_{OSSTL3_I}		SSTL3 I	–0.4	–0.5	ns
T_{OSSTL3_II}		SSTL3 II	–0.9	–1.1	ns
T_{OCTT}		CTT	–0.5	–0.6	ns
T_{OAGP}		AGP	–0.8	–1.0	ns

Notes:
1. Output timing is measured at 1.4V with 35 pF external capacitive load for LVTTL. For other I/O standards and different loads, see the tables "Constants for Calculating TIOOP" and "Delay Measurement Methodology," page 60.

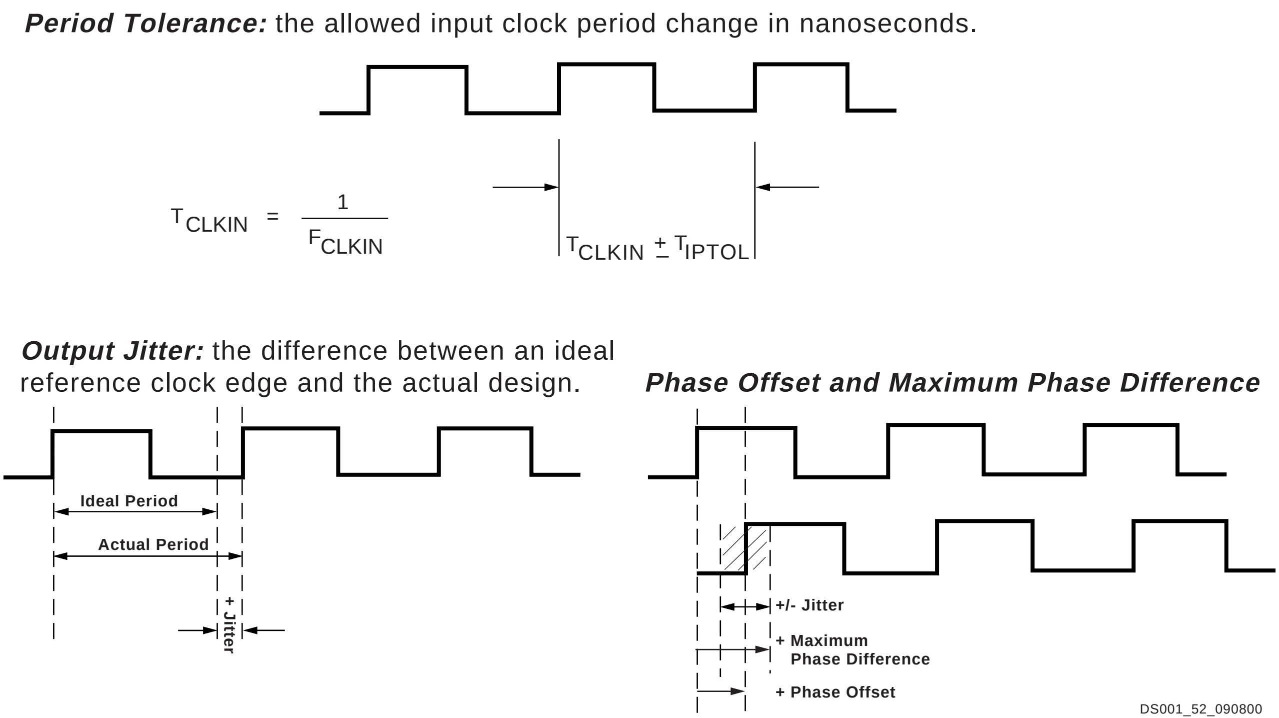


Figure 52: **Period Tolerance and Clock Jitter**

XC2S50 Device Pinouts *(Continued)*

XC2S50 Pad Name		TQ144	PQ208	FG256	Bndry Scan
Function	Bank				
I/O	0	-	-	D8	83
I/O	0	-	P188	A6	86
I/O, V_{REF}	0	P12	P189	B7	89
GND	-	-	P190	GND*	-
I/O	0	-	P191	C8	92
I/O	0	-	P192	D7	95
I/O	0	-	P193	E7	98
I/O	0	P11	P194	C7	104
I/O	0	P10	P195	B6	107
V_{CCINT}	-	P9	P196	V_{CCINT}*	-
V_{CCO}	0	-	P197	V_{CCO} Bank 0*	-
GND	-	P8	P198	GND*	-
I/O	0	P7	P199	A5	110
I/O	0	P6	P200	C6	113
I/O	0	-	P201	B5	116
I/O	0	-	-	D6	119
I/O	0	-	P202	A4	122
I/O, V_{REF}	0	P5	P203	B4	125
GND	-	-	-	GND*	-
I/O	0	-	P204	E6	128
I/O	0	-	-	D5	131
I/O	0	P4	P205	A3	134
I/O	0	-	-	C5	137
I/O	0	P3	P206	B3	140
TCK	-	P2	P207	C4	-
V_{CCO}	0	P1	P208	V_{CCO} Bank 0*	-
V_{CCO}	7	P144	P208	V_{CCO} Bank 7*	-

04/18/01

Notes:
1. IRDY and TRDY can only be accessed when using Xilinx PCI cores.
2. Pads labelled GND*, V_{CCINT}*, V_{CCO} Bank 0*, V_{CCO} Bank 1*, V_{CCO} Bank 2*, V_{CCO} Bank 3*, V_{CCO} Bank 4*, V_{CCO} Bank 5*, V_{CCO} Bank 6*, V_{CCO} Bank 7* are internally bonded to independent ground or power planes within the package.
3. See "VCCO Banks" for details on V_{CCO} banking.

Additional XC2S50 Package Pins

TQ144

Not Connected Pins					
P104	P105	-	-	-	-

11/02/00

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	Bank	TQ144	PQ208	FG256	FG456	Bndry Scan
V_{CCINT}	-	-	P38	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	6	-	P39	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P119	P40	GND*	GND*	-
I/O	6	P118	P41	K4	T1	314
I/O, V_{REF}	6	P117	P42	M1	R4	317
I/O	6	-	-	-	T2	320
I/O	6	P116	P43	L4	U1	323
I/O	6	-	-	M2	R5	326
I/O	6	-	P44	L3	U2	332
I/O, V_{REF}	6	P115	P45	N1	T3	335
V_{CCO}	6	-	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	-	-	GND*	GND*	-
I/O	6	-	P46	P1	T4	338
I/O	6	-	-	L5	W1	341
I/O	6	-	-	-	U4	344
I/O	6	P114	P47	N2	Y1	347
I/O	6	-	-	M4	W2	350
I/O	6	P113	P48	R1	Y2	356
I/O	6	P112	P49	M3	W3	359
M1	-	P111	P50	P2	U5	362
GND	-	P110	P51	GND*	GND*	-
M0	-	P109	P52	N3	AB2	363
V_{CCO}	6	P108	P53	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
V_{CCO}	5	P107	P53	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
M2	-	P106	P54	R3	Y4	364
I/O	5	-	-	N5	V7	374
I/O	5	P103	P57	T2	Y6	377
I/O	5	-	-	-	AA4	380
I/O	5	-	-	P5	W6	383
I/O	5	-	P58	T3	Y7	386
GND	-	-	-	GND*	GND*	-
V_{CCO}	5	-	-	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
I/O, V_{REF}	5	P102	P59	T4	AA5	389
I/O	5	-	P60	M6	AB5	392
I/O	5	-	-	T5	AB6	398
I/O	5	P101	P61	N6	AA7	401
I/O	5	-	-	-	W7	404

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	Bank	TQ144	PQ208	FG256	FG456	Bndry Scan
I/O, V_{REF}	5	P100	P62	R5	W8	407
I/O	5	P99	P63	P6	Y8	410
GND	-	P98	P64	GND*	GND*	-
V_{CCO}	5	-	P65	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
V_{CCINT}	-	P97	P66	V_{CCINT}*	V_{CCINT}*	-
I/O	5	P96	P67	R6	AA8	413
I/O	5	P95	P68	M7	V9	416
I/O	5	-	-	-	AB9	419
I/O	5	-	P69	N7	Y9	422
I/O	5	-	P70	T6	W10	428
I/O	5	-	P71	P7	AB10	431
GND	-	-	P72	GND*	GND*	-
I/O, V_{REF}	5	P94	P73	P8	Y10	434
I/O	5	-	P74	R7	V11	437
I/O	5	-	-	T7	W11	440
I/O	5	P93	P75	T8	AB11	443
V_{CCINT}	-	P92	P76	V_{CCINT}*	V_{CCINT}*	-
I, GCK1	5	P91	P77	R8	Y11	455
V_{CCO}	5	P90	P78	V_{CCO} Bank 5*	V_{CCO} Bank 5*	-
V_{CCO}	4	P90	P78	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
GND	-	P89	P79	GND*	GND*	-
I, GCK0	4	P88	P80	N8	W12	456
I/O	4	P87	P81	N9	U12	460
I/O	4	P86	P82	R9	Y12	466
I/O	4	-	-	N10	AA12	469
I/O	4	-	P83	T9	AB13	472
I/O, V_{REF}	4	P85	P84	P9	AA13	475
GND	-	-	P85	GND*	GND*	-
I/O	4	-	P86	M10	Y13	478
I/O	4	-	P87	R10	V13	481
I/O	4	-	P88	P10	AA14	487
I/O	4	-	-	-	V14	490
I/O	4	P84	P89	T10	AB15	493
I/O	4	P83	P90	R11	AA15	496
V_{CCINT}	-	P82	P91	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	4	-	P92	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
GND	-	P81	P93	GND*	GND*	-
I/O	4	P80	P94	M11	Y15	499

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	**Bank**	**TQ144**	**PQ208**	**FG256**	**FG456**	**Bndry Scan**
I/O	2	-	-	F12	G20	695
I/O	2	-	P149	E15	F19	701
I/O, V_{REF}	2	P41	P150	F13	F21	704
V_{CCO}	2	-	-	V_{CCO} Bank 2*	V_{CCO} Bank 2*	-
GND	-	-	-	GND*	GND*	-
I/O	2	-	P151	E14	F20	707
I/O	2	-	-	C16	F18	710
I/O	2	-	-	-	E21	713
I/O	2	P40	P152	E13	D22	716
I/O	2	-	-	B16	E20	719
I/O (DIN, D0)	2	P39	P153	D14	D20	725
I/O (DOUT, BUSY)	2	P38	P154	C15	C21	728
CCLK	2	P37	P155	D15	B22	731
V_{CCO}	2	P36	P156	V_{CCO} Bank 2*	V_{CCO} Bank 2*	-
V_{CCO}	1	P35	P156	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
TDO	2	P34	P157	B14	A21	-
GND	-	P33	P158	GND*	GND*	-
TDI	-	P32	P159	A15	B20	-
I/O ($\overline{CS}$)	1	P31	P160	B13	C19	0
I/O ($\overline{WRITE}$)	1	P30	P161	C13	A20	3
I/O	1	-	-	C12	D17	9
I/O	1	P29	P162	A14	A19	12
I/O	1	-	-	-	B18	15
I/O	1	-	-	D12	C17	18
I/O	1	-	P163	B12	D16	21
GND	-	-	-	GND*	GND*	-
V_{CCO}	1	-	-	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
I/O, V_{REF}	1	P28	P164	C11	A18	24
I/O	1	-	P165	A13	B17	27
I/O	1	-	-	D11	D15	33
I/O	1	-	P166	A12	C16	36
I/O	1	-	-	-	D14	39
I/O, V_{REF}	1	P27	P167	E11	E14	42
I/O	1	P26	P168	B11	A16	45
GND	-	P25	P169	GND*	GND*	-

XC2S100 Device Pinouts *(Continued)*

XC2S100 Pad Name						
Function	**Bank**	**TQ144**	**PQ208**	**FG256**	**FG456**	**Bndry Scan**
V_{CCO}	1	-	P170	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
V_{CCINT}	-	P24	P171	V_{CCINT}*	V_{CCINT}*	-
I/O	1	P23	P172	A11	C15	48
I/O	1	P22	P173	C10	B15	51
I/O	1	-	-	-	F12	54
I/O	1	-	P174	B10	C14	57
I/O	1	-	P175	D10	D13	63
I/O	1	-	P176	A10	C13	66
GND	-	-	P177	GND*	GND*	-
I/O, V_{REF}	1	P21	P178	B9	B13	69
I/O	1	-	P179	E10	E12	72
I/O	1	-	-	A9	B12	75
I/O	1	P20	P180	D9	D12	78
I/O	1	P19	P181	A8	D11	84
I, GCK2	1	P18	P182	C9	A11	90
GND	-	P17	P183	GND*	GND*	-
V_{CCO}	1	P16	P184	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
V_{CCO}	0	P16	P184	V_{CCO} Bank 0*	V_{CCO} Bank 0*	-
I, GCK3	0	P15	P185	B8	C11	91
V_{CCINT}	-	P14	P186	V_{CCINT}*	V_{CCINT}*	-
I/O	0	P13	P187	A7	A10	101
I/O	0	-	-	D8	B10	104

XC2S150 Device Pinouts

XC2S150 Pad Name		PQ208	FG256	FG456	Bndry Scan
Function	Bank				
GND	-	P1	GND*	GND*	-
TMS	-	P2	D3	D3	-
I/O	7	P3	C2	B1	221
I/O	7	-	-	E4	224
I/O	7	-	-	C1	227
I/O	7	-	A2	F5	230
GND	-	-	GND*	GND*	-
I/O	7	P4	B1	D2	233
I/O	7	-	-	E3	236
I/O	7	-	-	F4	239
I/O	7	-	E3	G5	242
I/O	7	P5	D2	F3	245
GND	-	-	GND*	GND*	-
V_{CCO}	7	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P6	C1	E2	248
I/O	7	P7	F3	E1	251
I/O	7	-	-	G4	254
I/O	7	-	-	G3	257
I/O	7	-	E2	H5	260
I/O	7	P8	E4	F2	263
I/O	7	-	-	F1	266
I/O, V_{REF}	7	P9	D1	H4	269
I/O	7	P10	E1	G1	272
GND	-	P11	GND*	GND*	-
V_{CCO}	7	P12	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCINT}	-	P13	V_{CCINT}*	V_{CCINT}*	-
I/O	7	P14	F2	H3	275
I/O	7	P15	G3	H2	278
I/O	7	-	-	H1	284
I/O	7	-	F1	J5	287
I/O	7	P16	F4	J2	290
I/O	7	-	-	J3	293
I/O	7	P17	F5	K5	299
I/O	7	P18	G2	K1	302
GND	-	P19	GND*	GND*	-
V_{CCO}	7	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P20	H3	K3	305
I/O	7	P21	G4	K4	308
I/O	7	-	H2	L6	311

XC2S150 Device Pinouts *(Continued)*

XC2S150 Pad Name		PQ208	FG256	FG456	Bndry Scan
Function	Bank				
I/O	7	P22	G5	L1	314
I/O	7	-	-	L5	317
I/O	7	P23	H4	L4	320
I/O, IRDY(1)	7	P24	G1	L3	323
GND	-	P25	GND*	GND*	-
V_{CCO}	7	P26	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCO}	6	P26	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
I/O, TRDY(1)	6	P27	J2	M1	326
V_{CCINT}	-	P28	V_{CCINT}*	V_{CCINT}*	-
I/O	6	-	-	M6	332
I/O	6	P29	H1	M3	335
I/O	6	-	J4	M4	338
I/O	6	P30	J1	M5	341
I/O, V_{REF}	6	P31	J3	N2	344
V_{CCO}	6	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P32	GND*	GND*	-
I/O	6	P33	K5	N3	347
I/O	6	P34	K2	N4	350
I/O	6	-	-	N5	356
I/O	6	P35	K1	P2	359
I/O	6	-	K3	P4	362
I/O	6	-	-	R1	365
I/O	6	P36	L1	P3	371
I/O	6	P37	L2	R2	374
V_{CCINT}	-	P38	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	6	P39	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P40	GND*	GND*	-
I/O	6	P41	K4	T1	377
I/O, V_{REF}	6	P42	M1	R4	380
I/O	6	-	-	T2	383
I/O	6	P43	L4	U1	386
I/O	6	-	M2	R5	389
I/O	6	-	-	V1	392
I/O	6	-	-	T5	395
I/O	6	P44	L3	U2	398
I/O, V_{REF}	6	P45	N1	T3	401
V_{CCO}	6	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	-	GND*	GND*	-

XC2S150 Device Pinouts *(Continued)*

XC2S150 Pad Name					Bndry
Function	Bank	PQ208	FG256	FG456	Scan
I/O	4	P90	R11	AA15	595
V_{CCINT}	-	P91	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	4	P92	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
GND	-	P93	GND*	GND*	-
I/O	4	P94	M11	Y15	598
I/O, V_{REF}	4	P95	T11	AB16	601
I/O	4	-	-	AB17	604
I/O	4	P96	N11	V15	607
I/O	4	-	R12	Y16	610
I/O	4	-	-	AA17	613
I/O	4	-	-	W16	616
I/O	4	P97	P11	AB18	619
I/O, V_{REF}	4	P98	T12	AB19	622
V_{CCO}	4	-	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
GND	-	-	GND*	GND*	-
I/O	4	P99	T13	Y17	625
I/O	4	-	N12	V16	628
I/O	4	-	-	AA18	631
I/O	4	-	-	W17	634
I/O	4	P100	R13	AB20	637
GND	-	-	GND*	GND*	-
I/O	4	-	P12	AA19	640
I/O	4	-	-	V17	643
I/O	4	-	-	Y18	646
I/O	4	P101	P13	AA20	649
I/O	4	P102	T14	W18	652
GND	-	P103	GND*	GND*	-
DONE	3	P104	R14	Y19	655
V_{CCO}	4	P105	V_{CCO} Bank 4*	V_{CCO} Bank 4*	-
V_{CCO}	3	P105	V_{CCO} Bank 3*	V_{CCO} Bank 3*	-
$\overline{\text{PROGRAM}}$	-	P106	P15	W20	658
I/O ($\overline{\text{INIT}}$)	3	P107	N15	V19	659
I/O (D7)	3	P108	N14	Y21	662
I/O	3	-	-	V20	665
I/O	3	-	-	AA22	668
I/O	3	-	T15	W21	671
GND	-	-	GND*	GND*	-
I/O	3	P109	M13	U20	674

XC2S150 Device Pinouts *(Continued)*

XC2S150 Pad Name					Bndry
Function	Bank	PQ208	FG256	FG456	Scan
I/O	3	-	-	U19	677
I/O	3	-	-	V21	680
I/O	3	-	R16	T18	683
I/O	3	P110	M14	W22	686
GND	-	-	GND*	GND*	-
V_{CCO}	3	-	V_{CCO} Bank 3*	V_{CCO} Bank 3*	-
I/O, V_{REF}	3	P111	L14	U21	689
I/O	3	P112	M15	T20	692
I/O	3	-	-	T19	695
I/O	3	-	-	V22	698
I/O	3	-	L12	T21	701
I/O	3	P113	P16	R18	704
I/O	3	-	-	U22	707
I/O, V_{REF}	3	P114	L13	R19	710
I/O (D6)	3	P115	N16	T22	713
GND	-	P116	GND*	GND*	-
V_{CCO}	3	P117	V_{CCO} Bank 3*	V_{CCO} Bank 3*	-
V_{CCINT}	-	P118	V_{CCINT}*	V_{CCINT}*	-
I/O (D5)	3	P119	M16	R21	716
I/O	3	P120	K14	P18	719
I/O	3	-	-	P19	725
I/O	3	-	L16	P20	728
I/O	3	P121	K13	P21	731
I/O	3	-	-	N19	734
I/O	3	P122	L15	N18	740
I/O	3	P123	K12	N20	743
GND	-	P124	GND*	GND*	-
V_{CCO}	3	-	V_{CCO} Bank 3*	V_{CCO} Bank 3*	-
I/O, V_{REF}	3	P125	K16	N21	746
I/O (D4)	3	P126	J16	N22	749
I/O	3	-	J14	M19	752
I/O	3	P127	K15	M20	755
I/O	3	-	-	M18	758
V_{CCINT}	-	P128	V_{CCINT}*	V_{CCINT}*	-
I/O, TRDY(1)	3	P129	J15	M22	764
V_{CCO}	3	P130	V_{CCO} Bank 3*	V_{CCO} Bank 3*	-
V_{CCO}	2	P130	V_{CCO} Bank 2*	V_{CCO} Bank 2*	-
GND	-	P131	GND*	GND*	-

XC2S200 Device Pinouts

XC2S200 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
GND	-	P1	GND*	GND*	-
TMS	-	P2	D3	D3	-
I/O	7	P3	C2	B1	257
I/O	7	-	-	E4	263
I/O	7	-	-	C1	266
I/O	7	-	A2	F5	269
GND	-	-	GND*	GND*	-
I/O, V_{REF}	7	P4	B1	D2	272
I/O	7	-	-	E3	275
I/O	7	-	-	F4	281
GND	-	-	GND*	GND*	-
I/O	7	-	E3	G5	284
I/O	7	P5	D2	F3	287
GND	-	-	GND*	GND*	-
V_{CCO}	7	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P6	C1	E2	290
I/O	7	P7	F3	E1	293
I/O	7	-	-	G4	296
I/O	7	-	-	G3	299
I/O	7	-	E2	H5	302
GND	-	-	GND*	GND*	-
I/O	7	P8	E4	F2	305
I/O	7	-	-	F1	308
I/O, V_{REF}	7	P9	D1	H4	314
I/O	7	P10	E1	G1	317
GND	-	P11	GND*	GND*	-
V_{CCO}	7	P12	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCINT}	-	P13	V_{CCINT}*	V_{CCINT}*	-
I/O	7	P14	F2	H3	320
I/O	7	P15	G3	H2	323
I/O	7	-	-	J4	326
I/O	7	-	-	H1	329
I/O	7	-	F1	J5	332
GND	-	-	GND*	GND*	-
I/O	7	P16	F4	J2	335
I/O	7	-	-	J3	338
I/O	7	-	-	J1	341
I/O	7	P17	F5	K5	344
I/O	7	P18	G2	K1	347
GND	-	P19	GND*	GND*	-

XC2S200 Device Pinouts *(Continued)*

XC2S200 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
V_{CCO}	7	-	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
I/O, V_{REF}	7	P20	H3	K3	350
I/O	7	P21	G4	K4	353
I/O	7	-	-	K2	359
I/O	7	-	H2	L6	362
I/O	7	P22	G5	L1	365
I/O	7	-	-	L5	368
I/O	7	P23	H4	L4	374
I/O, IRDY(1)	7	P24	G1	L3	377
GND	-	P25	GND*	GND*	-
V_{CCO}	7	P26	V_{CCO} Bank 7*	V_{CCO} Bank 7*	-
V_{CCO}	6	P26	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
I/O, TRDY(1)	6	P27	J2	M1	380
V_{CCINT}	-	P28	V_{CCINT}*	V_{CCINT}*	-
I/O	6	-	-	M6	389
I/O	6	P29	H1	M3	392
I/O	6	-	J4	M4	395
I/O	6	-	-	N1	398
I/O	6	P30	J1	M5	404
I/O, V_{REF}	6	P31	J3	N2	407
V_{CCO}	6	-	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P32	GND*	GND*	-
I/O	6	P33	K5	N3	410
I/O	6	P34	K2	N4	413
I/O	6	-	-	P1	416
I/O	6	-	-	N5	419
I/O	6	P35	K1	P2	422
GND	-	-	GND*	GND*	-
I/O	6	-	K3	P4	425
I/O	6	-	-	R1	428
I/O	6	-	-	P5	431
I/O	6	P36	L1	P3	434
I/O	6	P37	L2	R2	437
V_{CCINT}	-	P38	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	6	P39	V_{CCO} Bank 6*	V_{CCO} Bank 6*	-
GND	-	P40	GND*	GND*	-
I/O	6	P41	K4	T1	440
I/O, V_{REF}	6	P42	M1	R4	443

XC2S200 Device Pinouts *(Continued)*

XC2S200 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
V_{CCO}	1	P156	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
TDO	2	P157	B14	A21	-
GND	-	P158	GND*	GND*	-
TDI	-	P159	A15	B20	-
I/O ($\overline{CS}$)	1	P160	B13	C19	0
I/O ($\overline{WRITE}$)	1	P161	C13	A20	3
I/O	1	-	-	B19	9
I/O	1	-	-	C18	12
I/O	1	-	C12	D17	15
GND	-	-	GND*	GND*	-
I/O, V_{REF}	1	P162	A14	A19	18
I/O	1	-	-	B18	21
I/O	1	-	-	E16	27
I/O	1	-	D12	C17	30
I/O	1	P163	B12	D16	33
GND	-	-	GND*	GND*	-
V_{CCO}	1	-	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
I/O, V_{REF}	1	P164	C11	A18	36
I/O	1	P165	A13	B17	39
I/O	1	-	-	E15	42
I/O	1	-	-	A17	45
I/O	1	-	D11	D15	48
GND	-	-	GND*	GND*	-
I/O	1	P166	A12	C16	51
I/O	1	-	-	D14	54
I/O, V_{REF}	1	P167	E11	E14	60
I/O	1	P168	B11	A16	63
GND	-	P169	GND*	GND*	-
V_{CCO}	1	P170	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
V_{CCINT}	-	P171	V_{CCINT}*	V_{CCINT}*	-
I/O	1	P172	A11	C15	66
I/O	1	P173	C10	B15	69
I/O	1	-	-	E13	72
I/O	1	-	-	A15	75
I/O	1	-	-	F12	78
GND	-	-	GND*	GND*	-
I/O	1	P174	B10	C14	81
I/O	1	-	-	B14	84
I/O	1	-	-	A14	87

XC2S200 Device Pinouts *(Continued)*

XC2S200 Pad Name					
Function	Bank	PQ208	FG256	FG456	Bndry Scan
I/O	1	P175	D10	D13	90
I/O	1	P176	A10	C13	93
GND	-	P177	GND*	GND*	-
V_{CCO}	1	-	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
I/O, V_{REF}	1	P178	B9	B13	96
I/O	1	P179	E10	E12	99
I/O	1	-	-	A13	105
I/O	1	-	A9	B12	108
I/O	1	P180	D9	D12	111
I/O	1	-	-	C12	114
I/O	1	P181	A8	D11	120
I, GCK2	1	P182	C9	A11	126
GND	-	P183	GND*	GND*	-
V_{CCO}	1	P184	V_{CCO} Bank 1*	V_{CCO} Bank 1*	-
V_{CCO}	0	P184	V_{CCO} Bank 0*	V_{CCO} Bank 0*	-
I, GCK3	0	P185	B8	C11	127
V_{CCINT}	-	P186	V_{CCINT}*	V_{CCINT}*	-
I/O	0	-	-	E11	137
I/O	0	P187	A7	A10	140
I/O	0	-	D8	B10	143
I/O	0	-	-	F11	146
I/O	0	P188	A6	C10	152
I/O, V_{REF}	0	P189	B7	A9	155
V_{CCO}	0	-	V_{CCO} Bank 0*	V_{CCO} Bank 0*	-
GND	-	P190	GND*	GND*	-
I/O	0	P191	C8	B9	158
I/O	0	P192	D7	E10	161
I/O	0	-	-	C9	164
I/O	0	-	-	D10	167
I/O	0	P193	E7	A8	170
GND	-	-	GND*	GND*	-
I/O	0	-	-	D9	173
I/O	0	-	-	B8	176
I/O	0	-	-	C8	179
I/O	0	P194	C7	E9	182
I/O	0	P195	B6	A7	185
V_{CCINT}	-	P196	V_{CCINT}*	V_{CCINT}*	-
V_{CCO}	0	P197	V_{CCO} Bank 0*	V_{CCO} Bank 0*	-